**Product data sheet** 

# 1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- · Low threshold voltage
- · Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

# 3. Applications

- · Relay driver
- High-speed line driver
- · Low-side loadswitch
- · Switching circuits

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor	Per transistor							
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	60	V	
$V_{GS}$	gate-source voltage			-20	-	20	V	
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	210	mA	
Static characteristics (per transistor)								
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_{D}$ = 200 mA; $T_{j}$ = 25 °C		-	2.1	3.5	Ω	

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.



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# **5. Pinning information**

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1	□6 □5 □4	D1 D2
2	G1	gate TR1		
3	D2	drain TR2	0	G1 A A G2
4	S2	source TR2	1 2 3	
5	G2	gate TR2	TSSOP6 (SOT363)	N
6	D1	drain TR1		S1 S2 017aaa256

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package	ackage					
	Name	Description	Version				
NX138BKS	TSSOP6	plastic surface-mounted package; 6 leads	SOT363				

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# 7. Limiting values

### **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transisto	or			,		
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	60	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	210	mA
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	135	mA
		V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 25 °C		-	330	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	855	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	285	mW
			[1]	-	320	mW
		T <sub>sp</sub> = 25 °C		-	860	mW
Per device				,		
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain	n diode		'			,
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	170	mA
		· ·	-			

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

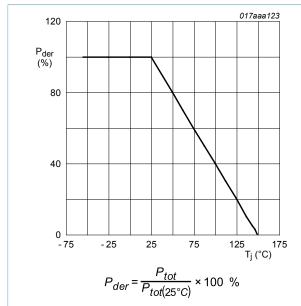


Fig. 1. MOSFET transistor: Normalized total power dissipation as a function of junction temperature

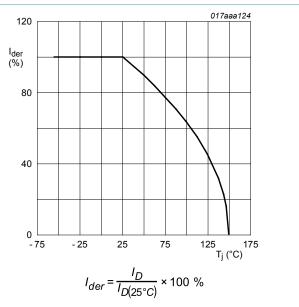


Fig. 2. MOSFET transistor: Normalized continuous drain current as a function of junction temperature

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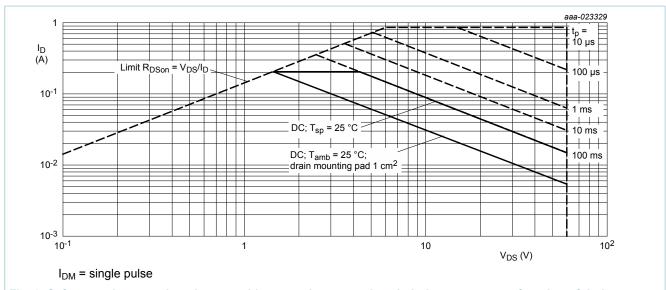


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

# 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
uig-a)	thermal resistance from junction to ambient		[1]	-	380	440	K/W
			[2]	-	340	390	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	125	145	K/W

Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint. Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1  $\rm cm^2$ .

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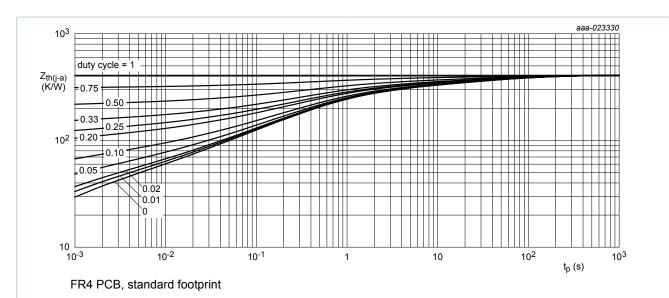


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

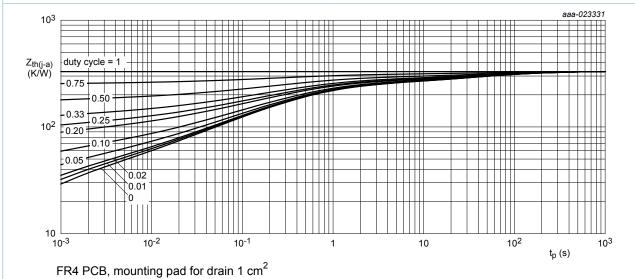


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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# 9. Characteristics

### **Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics (per transistor)					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.5	1	1.5	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μΑ
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-10	μΑ
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μΑ
		V <sub>GS</sub> = 5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	0.3	μΑ
		$V_{GS} = -5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-0.3	μΑ
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 25 °C	-	2.1	3.5	Ω
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 150 °C	-	4.3	7.2	Ω
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 170 mA; T <sub>j</sub> = 25 °C	-	2.2	3.8	Ω
		$V_{GS}$ = 2.5 V; $I_{D}$ = 75 mA; $T_{j}$ = 25 °C	-	2.6	5	Ω
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; $I_{D}$ = 200 mA; $T_{j}$ = 25 °C	-	0.7	-	S
Dynamic ch	naracteristics (per transist	or)	,	'		
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 30 V; I <sub>D</sub> = 200 mA; V <sub>GS</sub> = 10 V;	-	0.5	0.7	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	0.12	-	nC
$Q_{GD}$	gate-drain charge		-	0.12	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 30 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	20	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	3.1	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	2	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 30 V; $I_{D}$ = 200 mA; $V_{GS}$ = 10 V;	-	8	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	8	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	13	-	ns
t <sub>f</sub>	fall time		-	5	-	ns
Source-dra	in diode (per transistor)		'			,
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 200 mA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.9	1.2	V
						_

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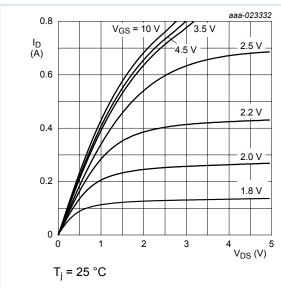


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

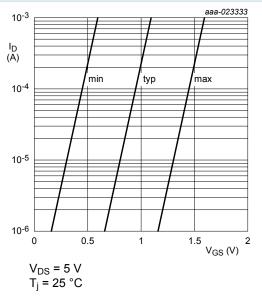


Fig. 7. Sub-threshold drain current as a function of gatesource voltage

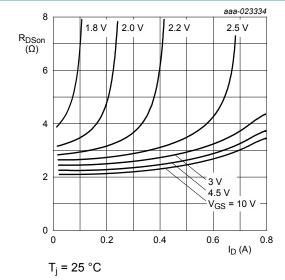


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

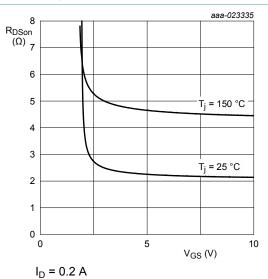


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

## 60 V, dual N-channel Trench MOSFET

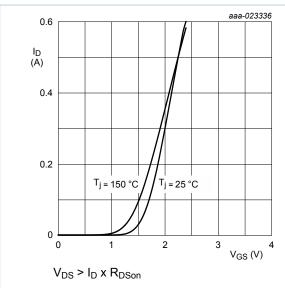


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

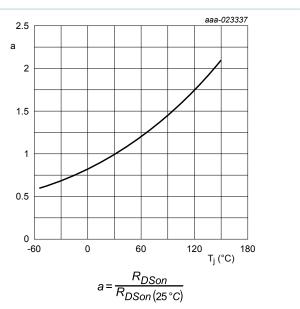


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

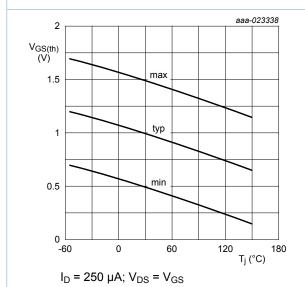


Fig. 12. Gate-source threshold voltage as a function of junction temperature

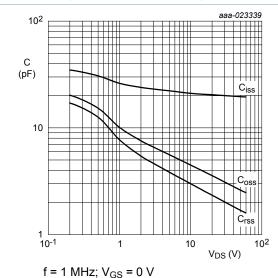


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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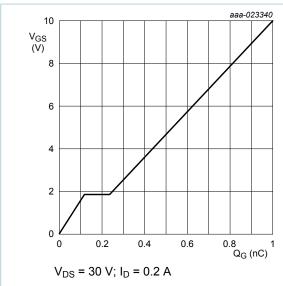


Fig. 14. Gate-source voltage as a function of gate charge; typical values

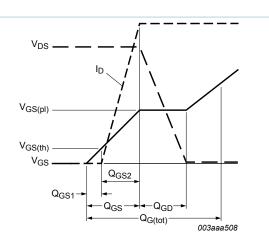


Fig. 15. MOSFET transistor: Gate charge waveform definitions

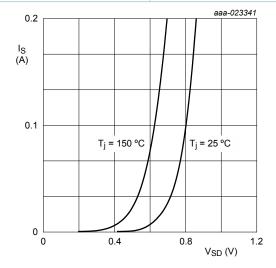
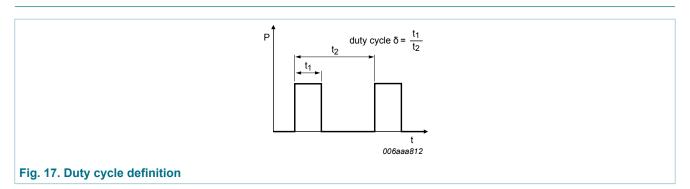


Fig. 16. Source current as a function of source-drain voltage; typical values

## 10. Test information

 $V_{GS} = 0 V$ 



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# 11. Package outline

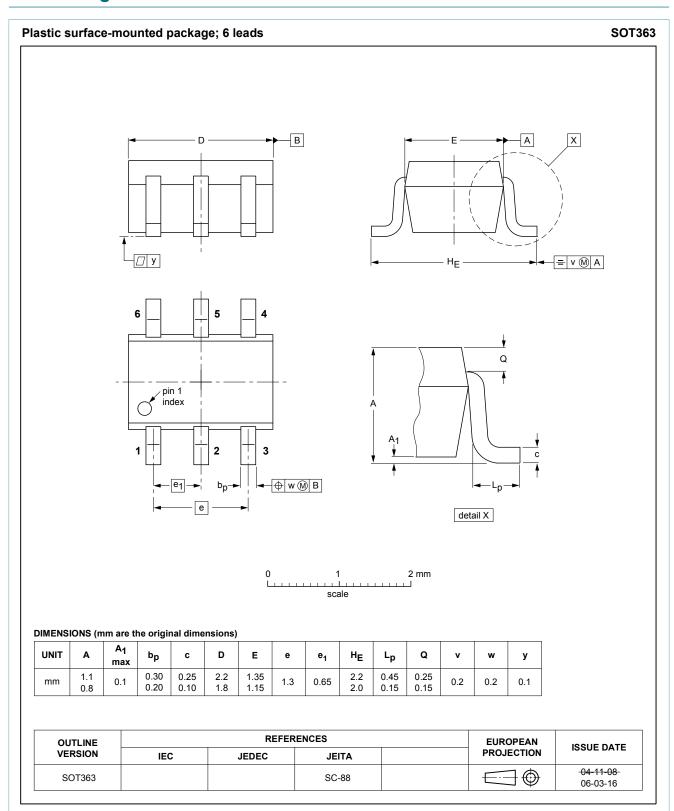
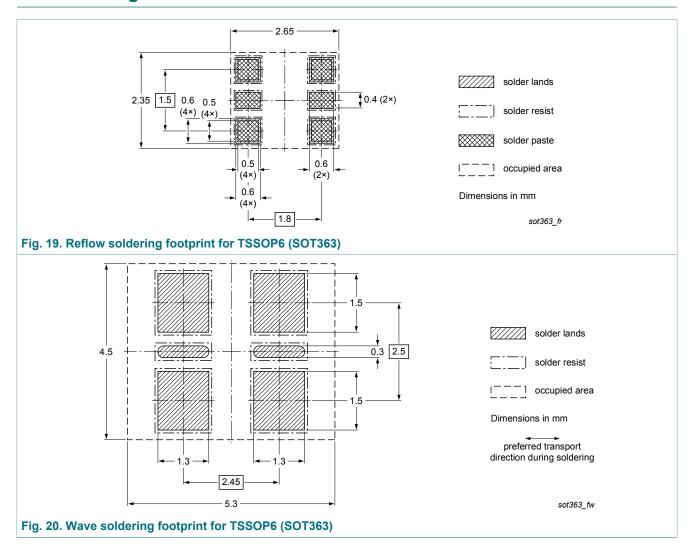


Fig. 18. Package outline TSSOP6 (SOT363)

## 60 V, dual N-channel Trench MOSFET

# 12. Soldering



**60 V, dual N-channel Trench MOSFET** 

# 13. Revision history

## **Table 7. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
NX138BKS v.1	20160615	Product data sheet	-	-

#### 60 V, dual N-channel Trench MOSFET

# 14. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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NX138BKS

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